

UNR911xJ Series (UN911xJ Series)

Silicon PNP epitaxial planar type

For digital circuits

■ Features

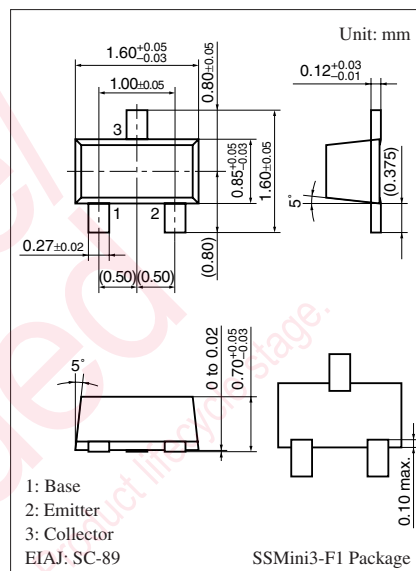
- Costs can be reduced through downsizing of the equipment and reduction of the number of parts.
- SS-Mini type package, allowing automatic insertion through tape packing.

■ Resistance by Part Number

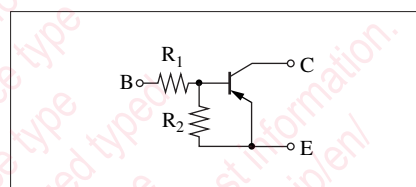
	Marking Symbol	(R ₁)	(R ₂)
• UNR9110J (UN9110J)	6L	47 kΩ	—
• UNR9111J (UN9111J)	6A	10 kΩ	10 kΩ
• UNR9112J (UN9112J)	6B	22 kΩ	22 kΩ
• UNR9113J (UN9113J)	6C	47 kΩ	47 kΩ
• UNR9114J (UN9114J)	6D	10 kΩ	47 kΩ
• UNR9115J (UN9115J)	6E	10 kΩ	—
• UNR9116J (UN9116J)	6F	4.7 kΩ	—
• UNR9117J (UN9117J)	6H	22 kΩ	—
• UNR9118J (UN9118J)	6I	0.51 kΩ	5.1 kΩ
• UNR9119J (UN9119J)	6K	1 kΩ	10 kΩ
• UNR911AJ	6X	100 kΩ	100 kΩ
• UNR911BJ	6Y	100 kΩ	—
• UNR911CJ	6Z	—	47 kΩ
• UNR911DJ (UN911DJ)	6M	47 kΩ	10 kΩ
• UNR911EJ (UN911EJ)	6N	47 kΩ	22 kΩ
• UNR911FJ (UN911FJ)	6O	4.7 kΩ	10 kΩ
• UNR911HJ (UN911HJ)	6P	2.2 kΩ	10 kΩ
• UNR911LJ (UN911LJ)	6Q	4.7 kΩ	4.7 kΩ
• UNR911MJ	EI	2.2 kΩ	47 kΩ
• UNR911NJ	EW	4.7 kΩ	47 kΩ
• UNR911TJ (UN911TJ)	EY	22 kΩ	47 kΩ
• UNR911VJ	FC	2.2 kΩ	2.2 kΩ

■ Absolute Maximum Ratings T_a = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V _{CBO}	−50	V
Collector-emitter voltage (Base open)	V _{CEO}	−50	V
Collector current	I _C	−100	mA
Total power dissipation	P _T	125	mW
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	−55 to +125	°C



Internal Connection



Note) The part numbers in the parenthesis show conventional part number.

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

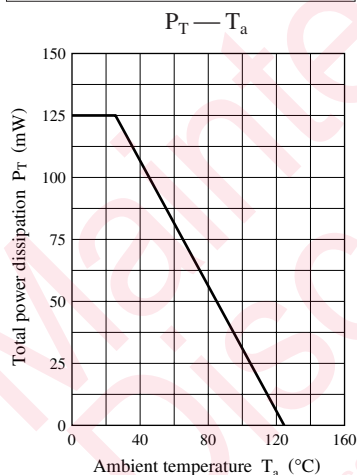
Parameter		Symbol	Conditions	Min	Typ	Max	Unit																																																																																			
Collector-base voltage (Emitter open)		V _{CBO}	I _C = -10 μA, I _E = 0	-50			V																																																																																			
Collector-emitter voltage (Base open)		V _{CEO}	I _C = -2 mA, I _B = 0	-50			V																																																																																			
Collector-base cutoff current (Emitter open)		I _{CBO}	V _{CB} = -50 V, I _E = 0			- 0.1	μA																																																																																			
Collector-base cutoff current (Emitter open)		I _{CEO}	V _{CE} = -50 V, I _B = 0			- 0.5	μA																																																																																			
Emitter-base cutoff current (Collector open)	UNR9115J/9116J/9117J/911BJ	I _{EBO}	V _{EB} = -6 V, I _C = 0			- 0.01	mA																																																																																			
	UNR9110J/9113J/911AJ					- 0.1																																																																																				
	UNR9112J/9114J/911DJ/ 911EJ/911MJ/911NJ/911TJ					- 0.2																																																																																				
	UNR9111J					- 0.5																																																																																				
	UNR911FJ/911HJ					-1.0																																																																																				
	UNR9119J					-1.5																																																																																				
	UNR9118J/911CJ/911LJ/911VJ					-2.0																																																																																				
	Forward current transfer ratio			UNR911VJ	h _{FE}	V _{CE} = -10 V, I _C = -5 mA		6		20	—																																																																															
UNR9118J/911LJ		20																																																																																								
UNR9119J/911DJ/911FJ/911HJ		30																																																																																								
UNR9111J		35																																																																																								
UNR9112J/911EJ		60																																																																																								
UNR9113J/9114J/911AJ/ 911CJ/911MJ		80																																																																																								
UNR911NJ/911TJ		80		400																																																																																						
UNR9110J/9115J/9116J/ 9117J/911BJ		160		460																																																																																						
Collector-emitter saturation voltage		V _{CE(sat)}	I _C = -10 mA, I _B = - 0.3 mA			- 0.25	V																																																																																			
UNR911VJ			I _C = -10 mA, I _B = -1.5 mA					Output voltage high-level		V _{OH}	V _{CC} = -5 V, V _B = - 0.5 V, R _L = 1 kΩ	-4.9			V	Output voltage low-level		V _{OL}	V _{CC} = -5 V, V _B = -2.5 V, R _L = 1 kΩ			- 0.2	V	UNR9113J/911BJ		V _{CC} = -5 V, V _B = -3.5 V, R _L = 1 kΩ				UNR911DJ		V _{CC} = -5 V, V _B = -10 V, R _L = 1 kΩ				UNR911EJ		V _{CC} = -5 V, V _B = -6 V, R _L = 1 kΩ				UNR911AJ		V _{CC} = -5 V, V _B = -5 V, R _L = 1 kΩ				Transition frequency		f _T	V _{CB} = -10 V, I _E = 1 mA, f = 200 MHz		80		MHz	UNR9113J		V _{CB} = -10 V, I _E = 1 mA, f = 200 MHz		150		UNR911AJ		V _{CB} = -10 V, I _E = 2 mA, f = 200 MHz		80		UNR911CJ		V _{CB} = -10 V, I _E = 2 mA, f = 200 MHz		150		Input resistance	UNR9118J	R ₁		-30%	0.51	+30%	kΩ	UNR9119J	1.0	UNR911HJ/911MJ/911VJ	2.2	UNR9116J/911FJ/911LJ/911NJ	4.7	UNR9111J/9114J/9115J	10	UNR9112J/9117J/911TJ
Output voltage high-level		V _{OH}	V _{CC} = -5 V, V _B = - 0.5 V, R _L = 1 kΩ	-4.9			V																																																																																			
Output voltage low-level		V _{OL}	V _{CC} = -5 V, V _B = -2.5 V, R _L = 1 kΩ			- 0.2	V																																																																																			
UNR9113J/911BJ			V _{CC} = -5 V, V _B = -3.5 V, R _L = 1 kΩ																																																																																							
UNR911DJ			V _{CC} = -5 V, V _B = -10 V, R _L = 1 kΩ																																																																																							
UNR911EJ			V _{CC} = -5 V, V _B = -6 V, R _L = 1 kΩ																																																																																							
UNR911AJ			V _{CC} = -5 V, V _B = -5 V, R _L = 1 kΩ																																																																																							
Transition frequency		f _T	V _{CB} = -10 V, I _E = 1 mA, f = 200 MHz		80		MHz																																																																																			
UNR9113J			V _{CB} = -10 V, I _E = 1 mA, f = 200 MHz		150																																																																																					
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UNR911CJ			V _{CB} = -10 V, I _E = 2 mA, f = 200 MHz		150																																																																																					
Input resistance	UNR9118J	R ₁		-30%	0.51	+30%	kΩ																																																																																			
	UNR9119J				1.0																																																																																					
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	UNR9116J/911FJ/911LJ/911NJ				4.7																																																																																					
	UNR9111J/9114J/9115J				10																																																																																					
	UNR9112J/9117J/911TJ				22																																																																																					
	UNR9110J/9113J/911DJ/911EJ				47																																																																																					
	UNR911AJ/911BJ				100																																																																																					

■ Electrical Characteristics (continued) $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

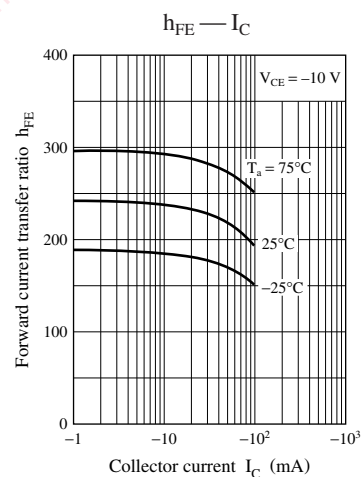
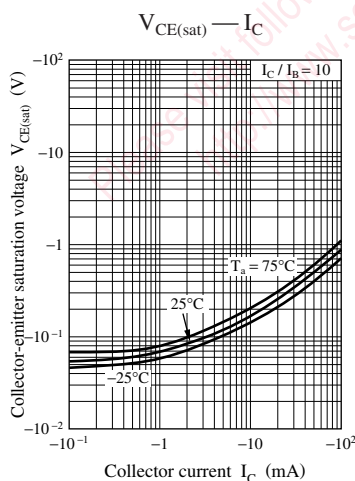
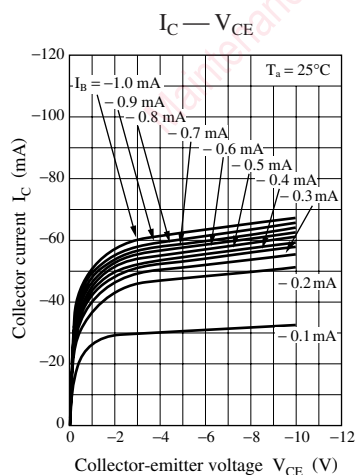
Parameter		Symbol	Conditions	Min	Typ	Max	Unit
Emitter-base resistance		UNR911CJ	R_2	-30%	47	+30%	$k\Omega$
Resistance ratio	UNR911MJ	R_1/R_2			0.047		—
	UNR911NJ				0.1		
	UNR9118J/9119J			0.08	0.10	0.12	
	UNR9114J			0.17	0.21	0.25	
	UNR911HJ			0.17	0.22	0.27	
	UNR911TJ				0.47		
	UNR911FJ			0.37	0.47	0.57	
	UNR911AJ/911VJ				1.0		
	UNR9111J/9112J/9113J/911LJ			0.8	1.0	1.2	
	UNR911EJ			1.70	2.14	2.60	
	UNR911DJ			3.7	4.7	5.7	

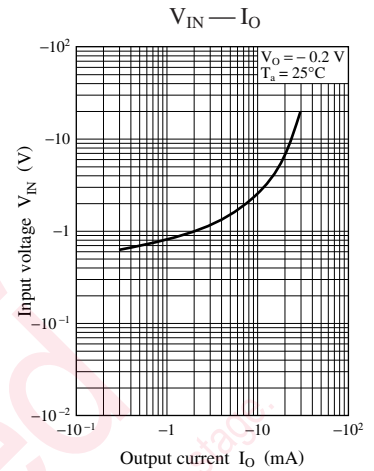
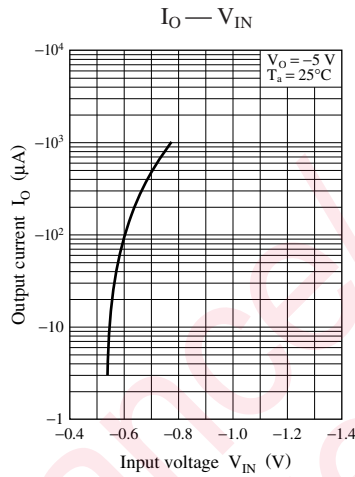
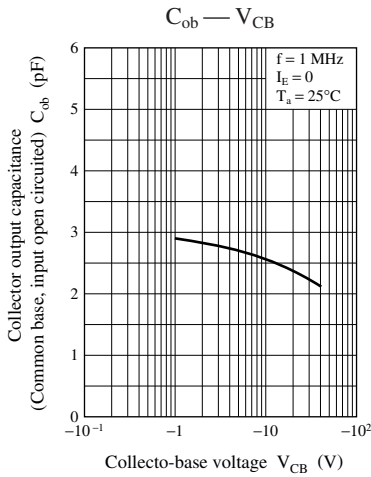
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

Common characteristics chart

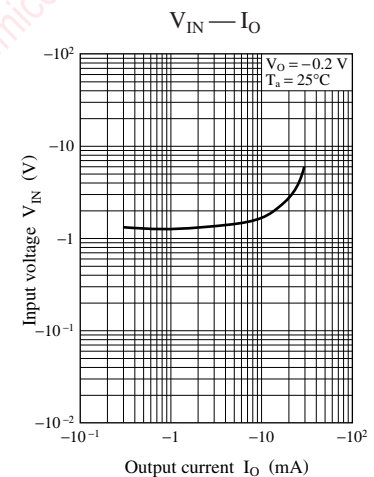
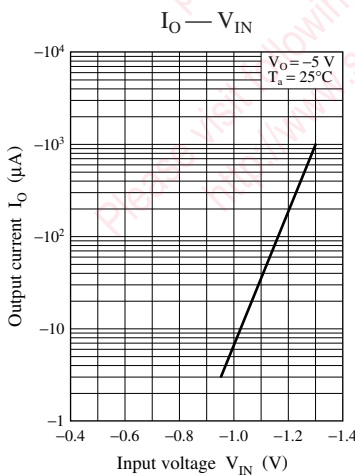
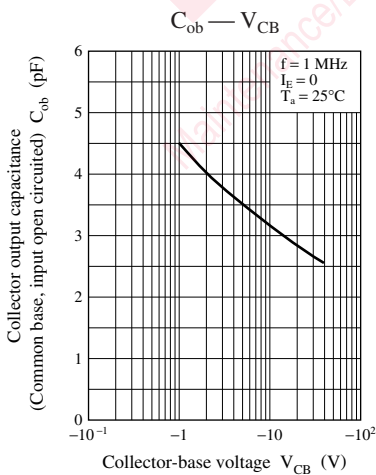
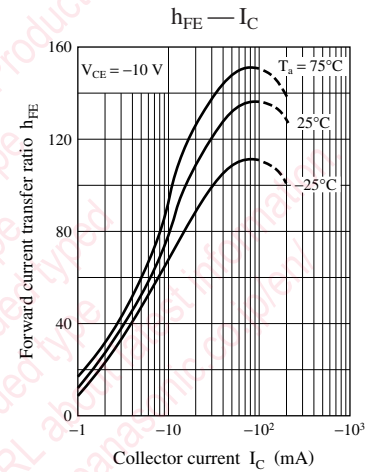
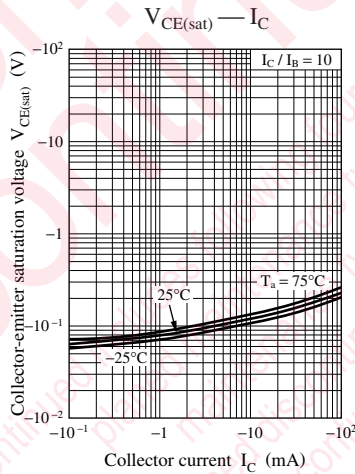
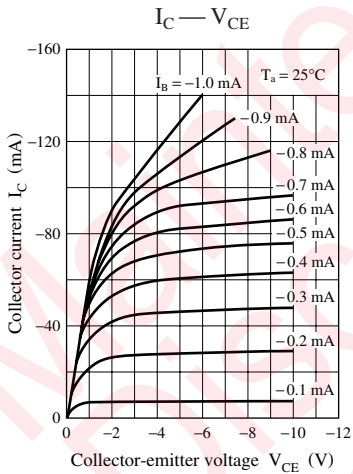


Characteristics charts of UNR9110J

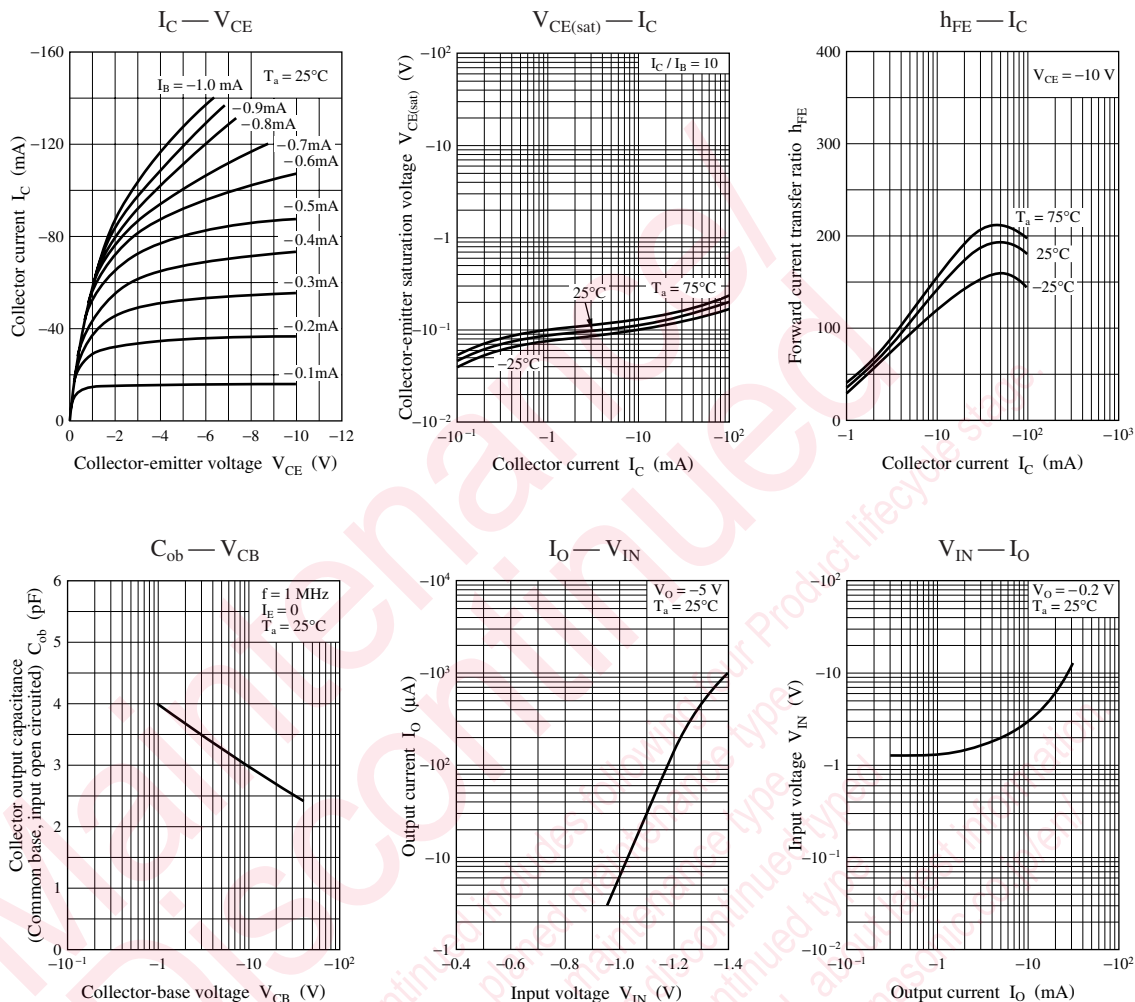




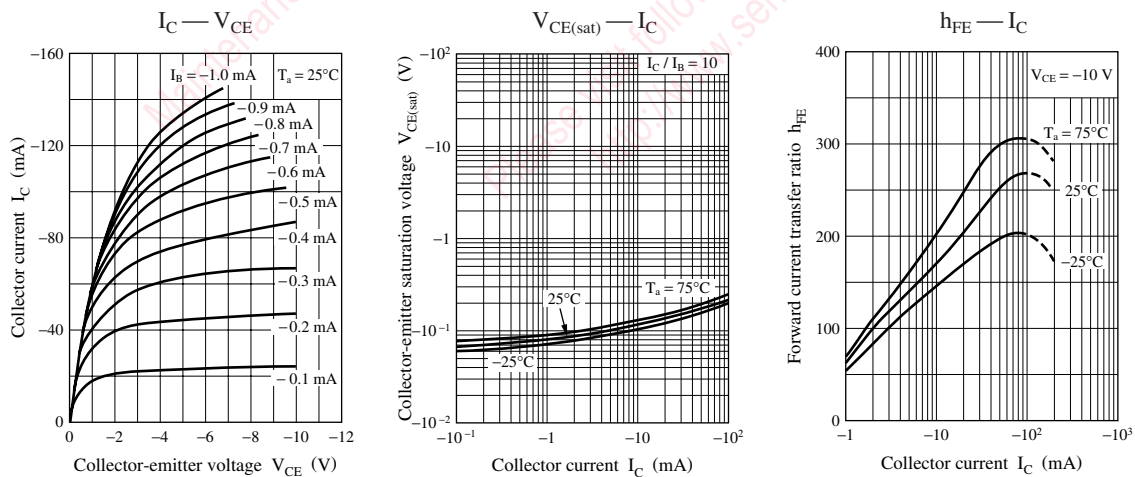
Characteristics charts of UNR9111J

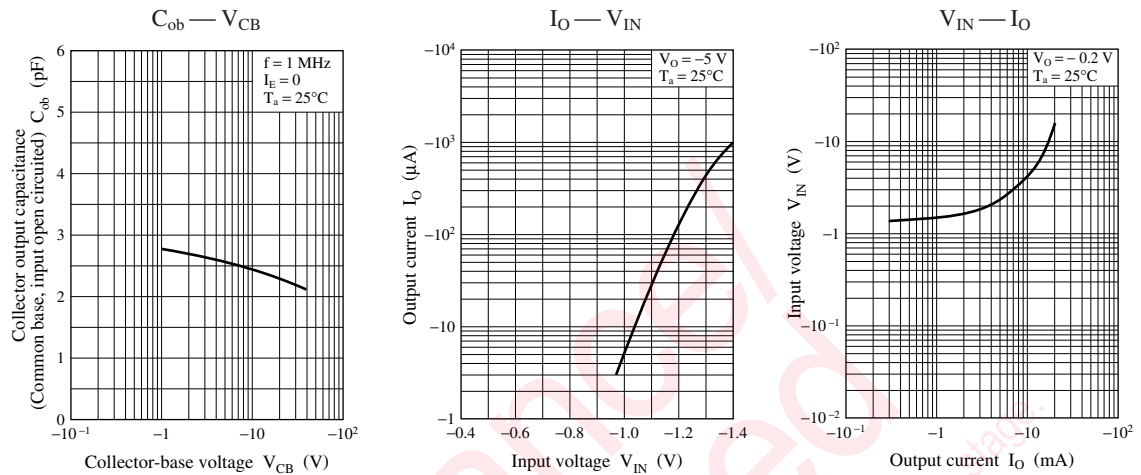


Characteristics charts of UNR9112J

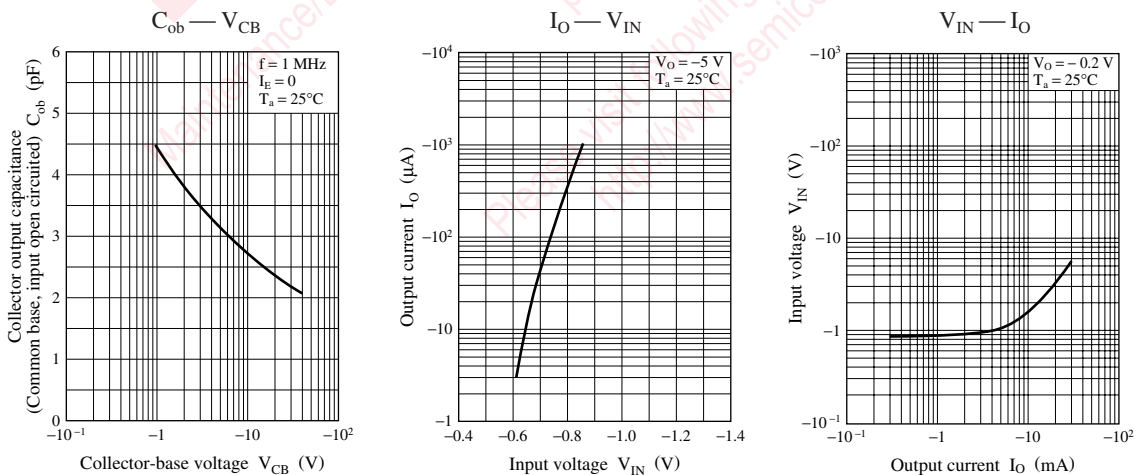
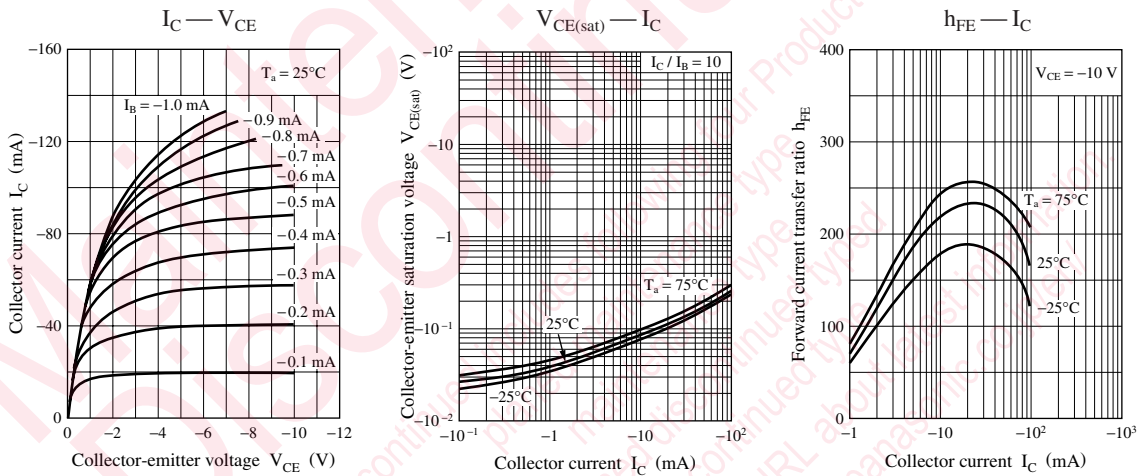


Characteristics charts of UNR9113J

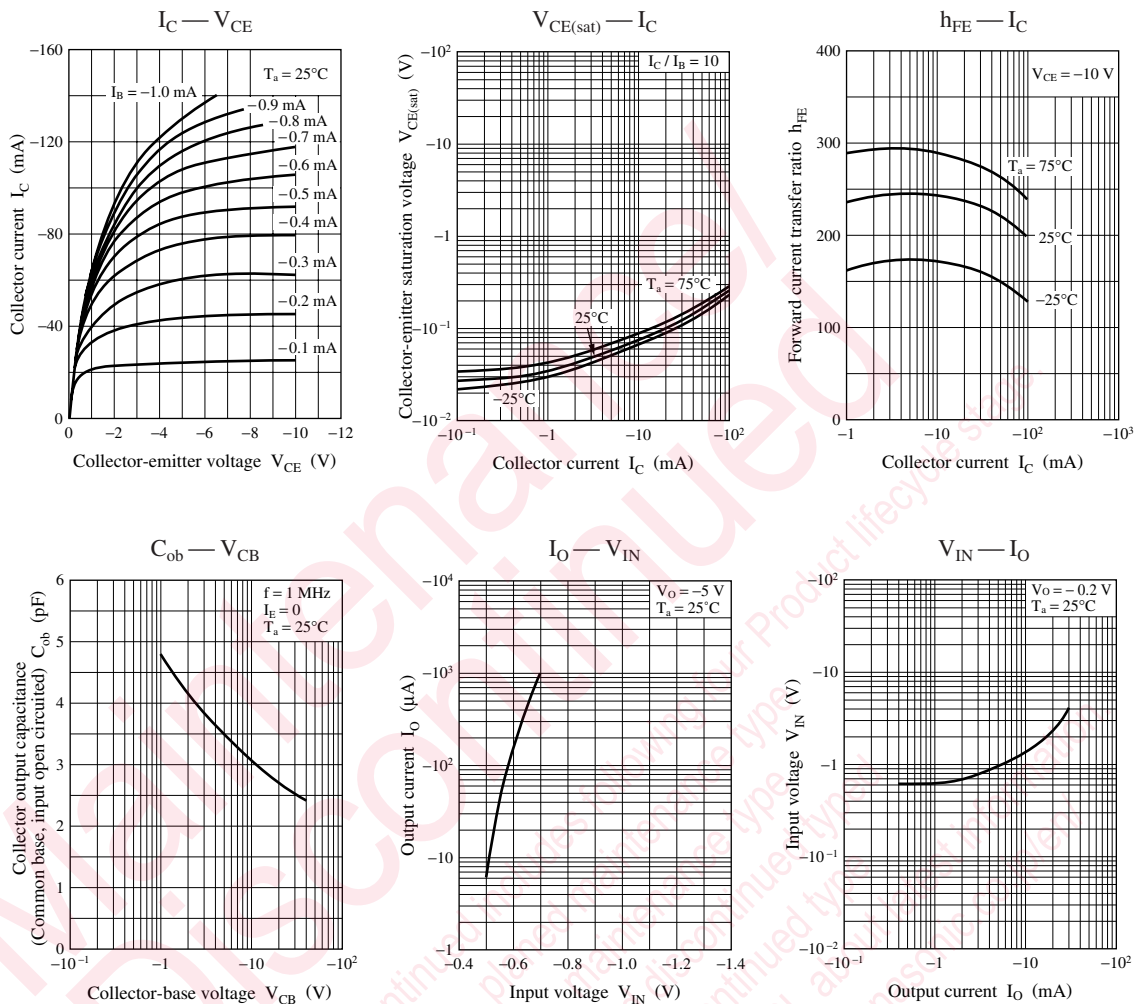




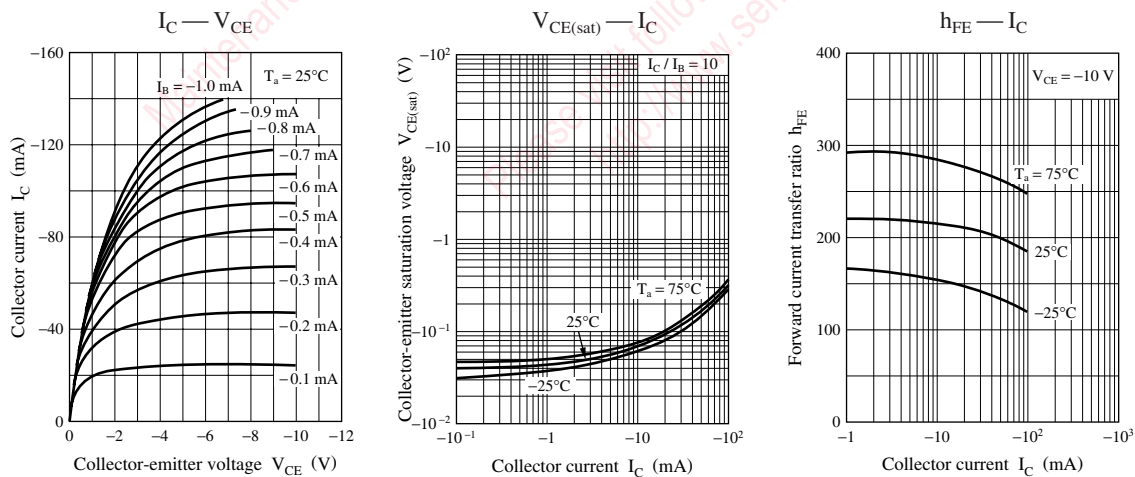
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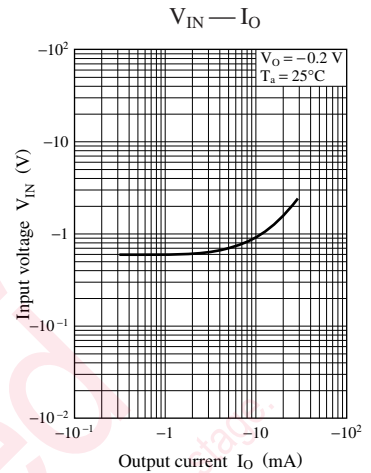
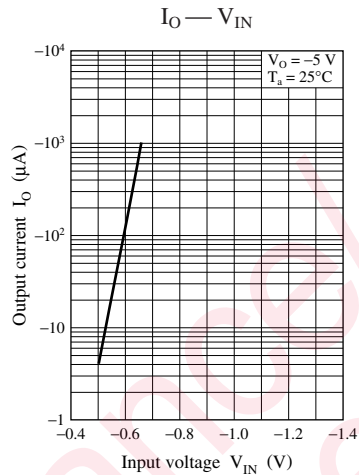
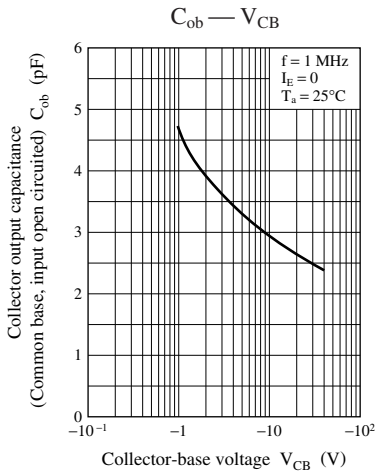


Characteristics charts of UNR9115J

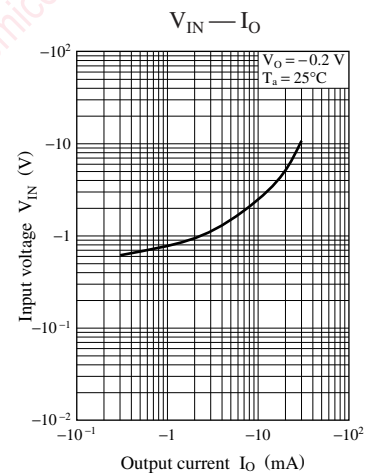
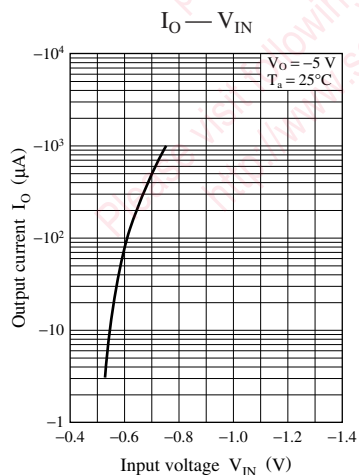
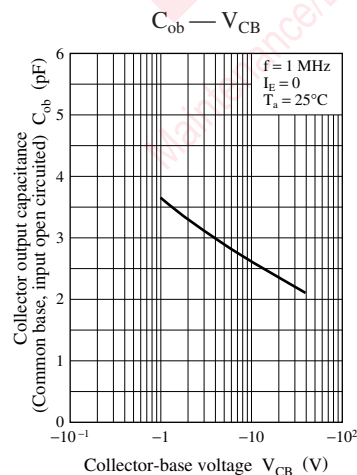
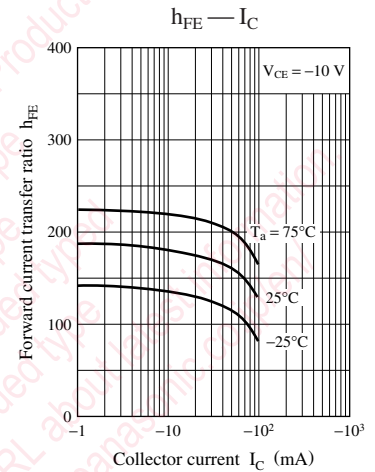
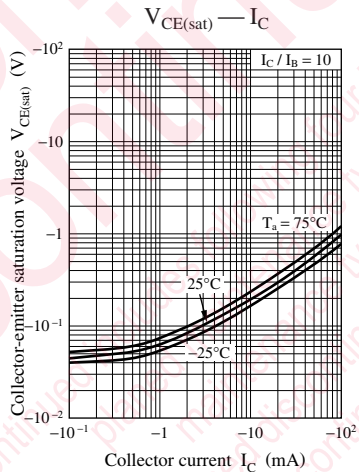
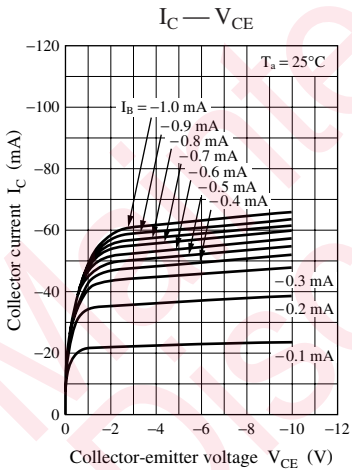


Characteristics charts of UNR9116J

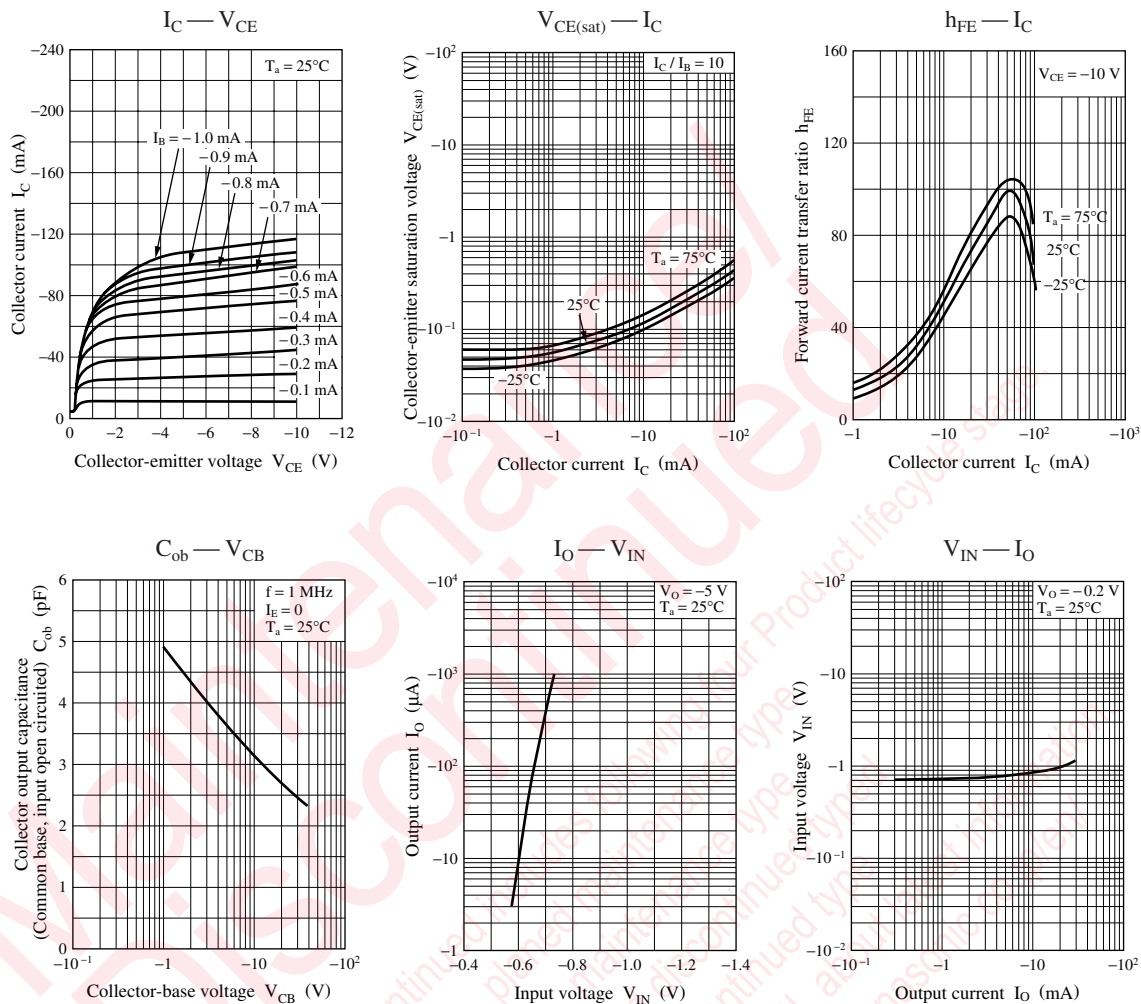




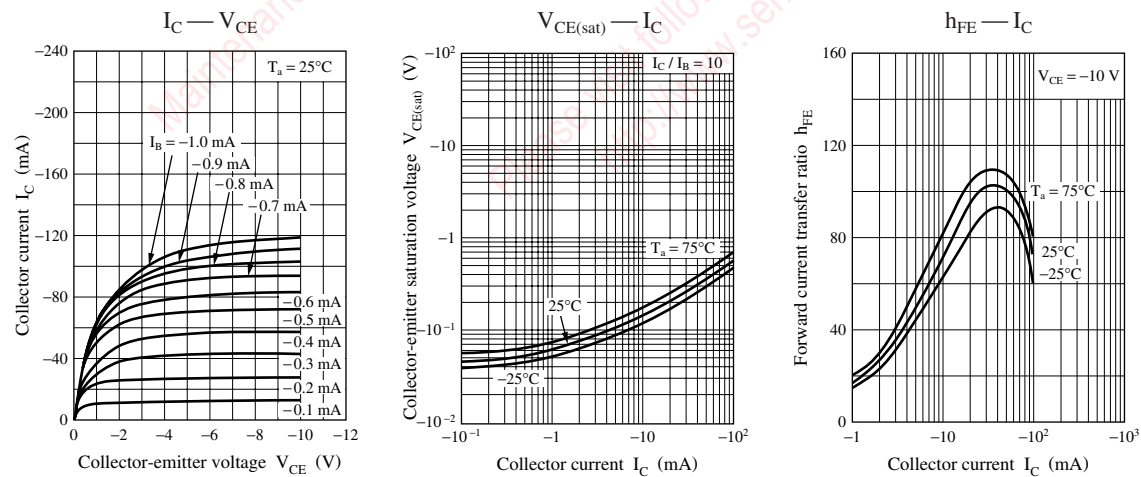
Characteristics charts of UNR9117J

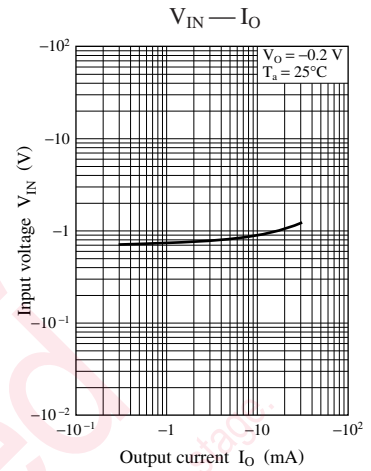
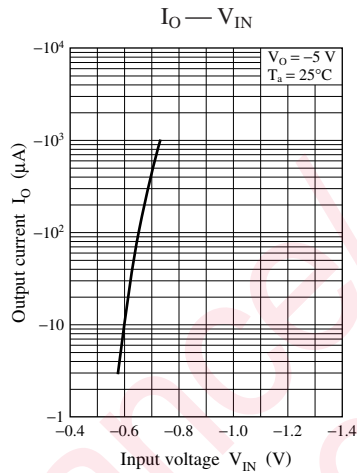
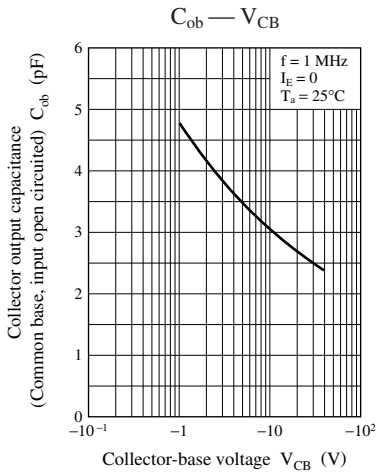


Characteristics charts of UNR9118J

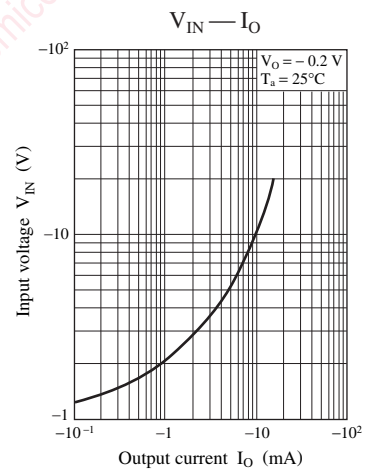
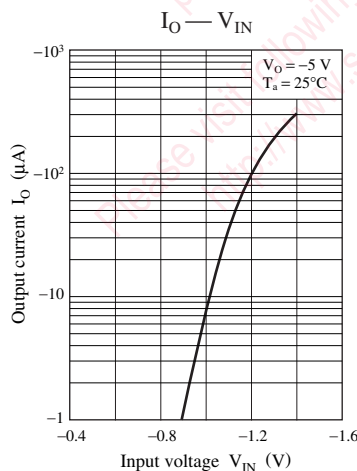
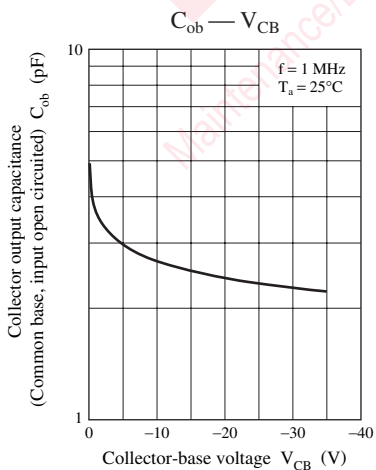
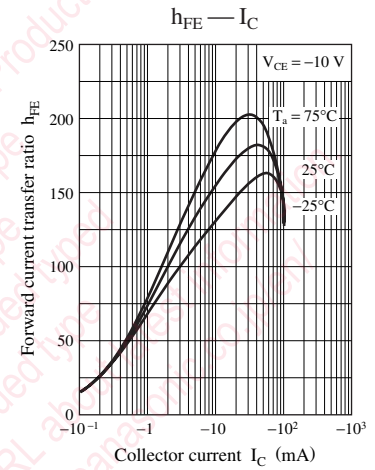
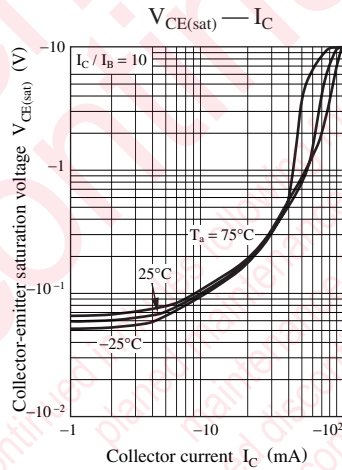
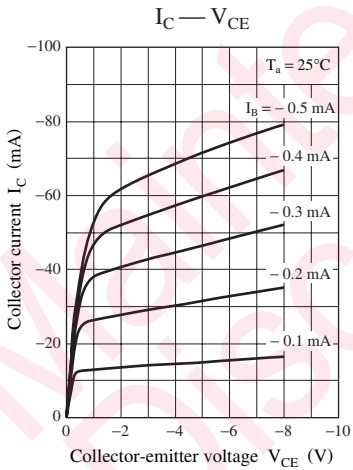


Characteristics charts of UNR9119J

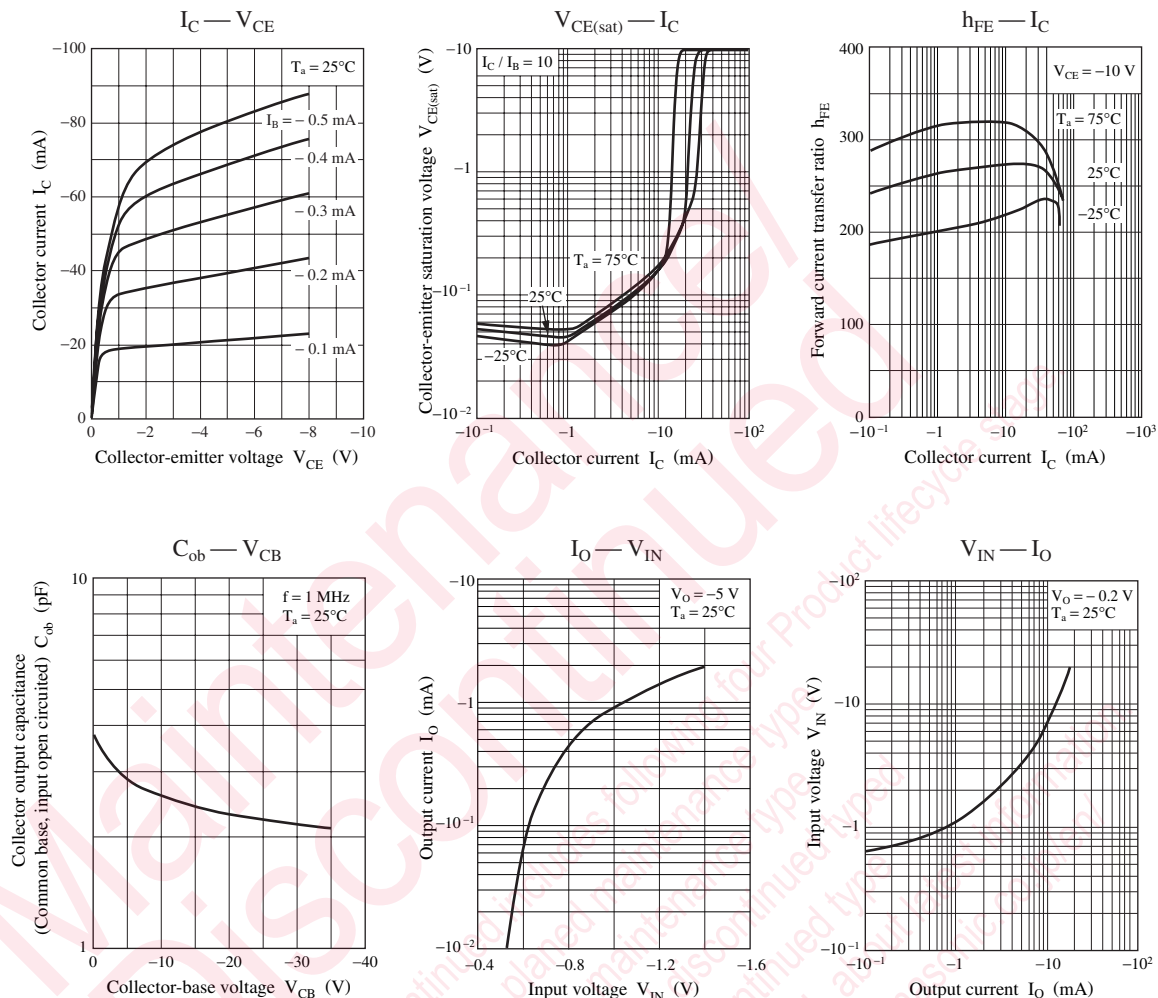




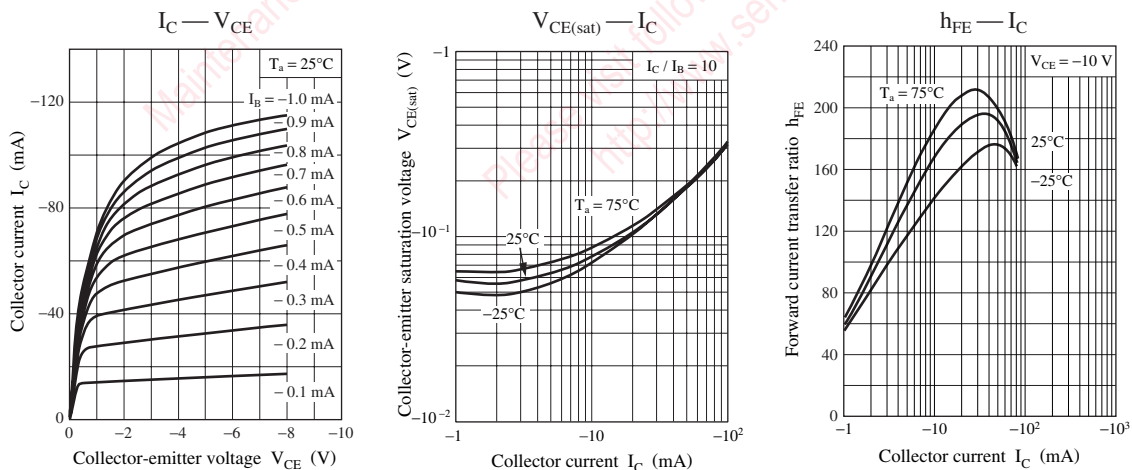
Characteristics charts of UNR911AJ

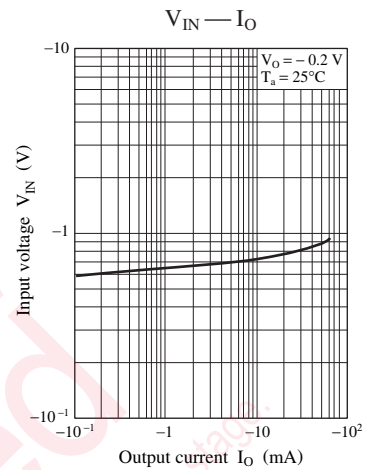
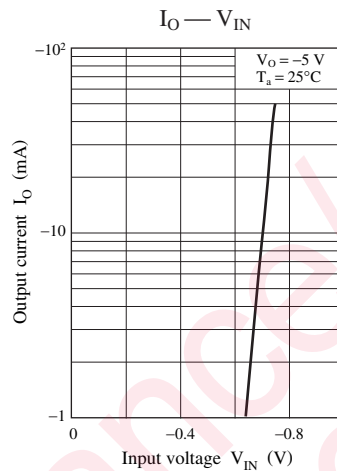
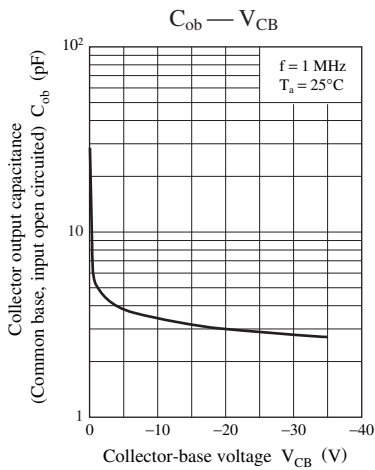


Characteristics charts of UNR911BJ

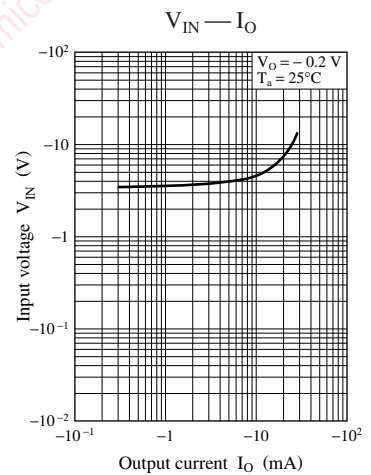
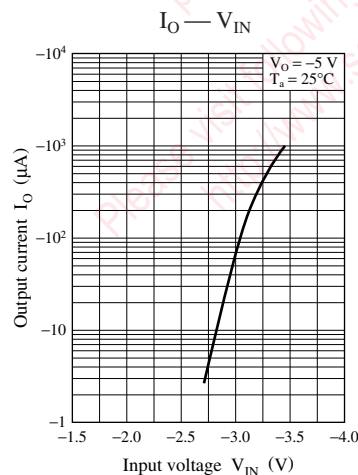
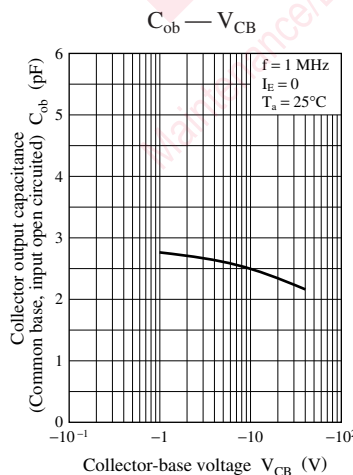
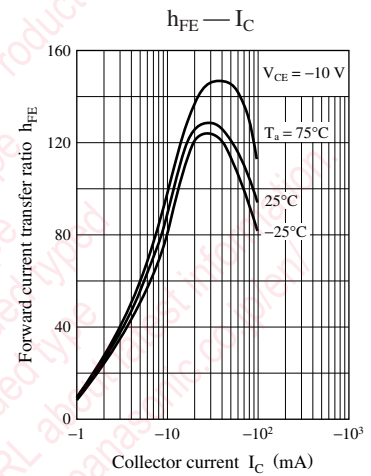
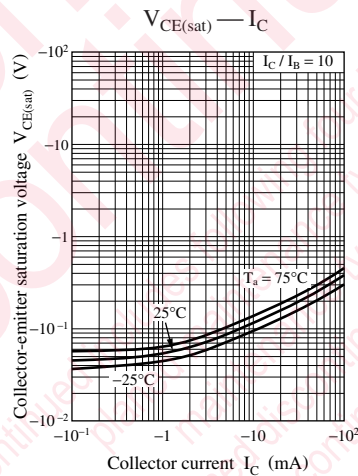
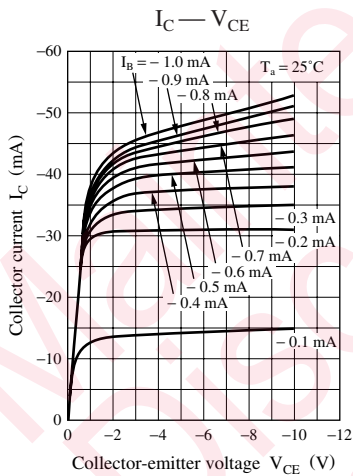


Characteristics charts of UNR911CJ

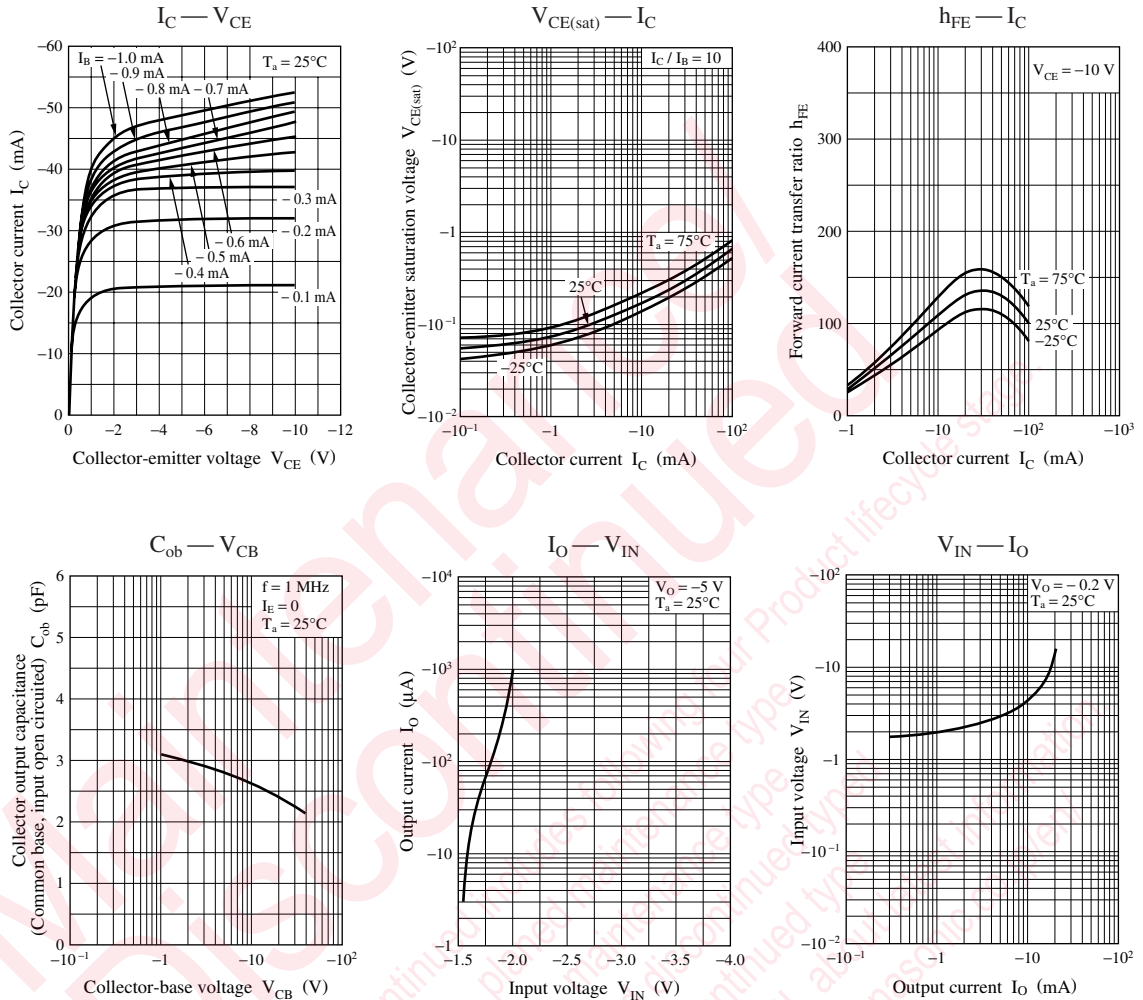




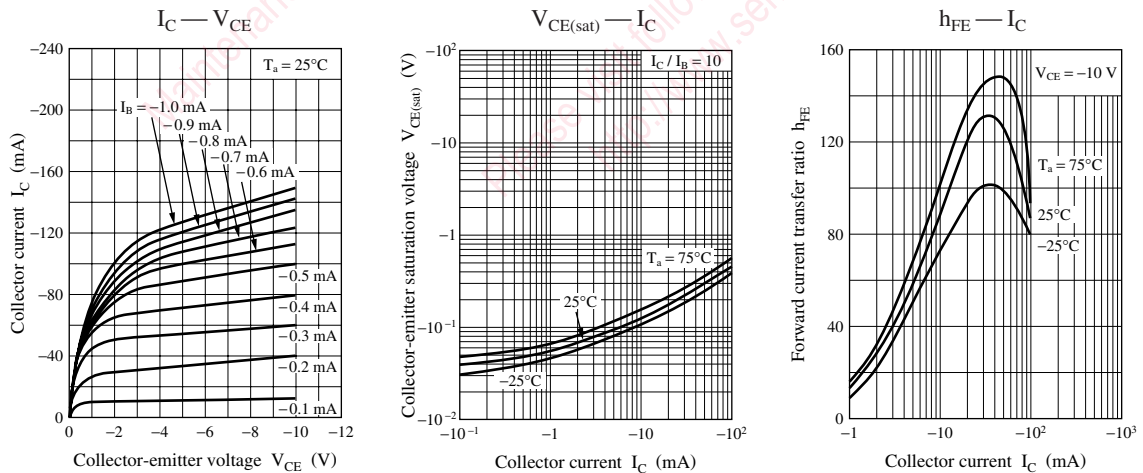
Characteristics charts of UNR911DJ

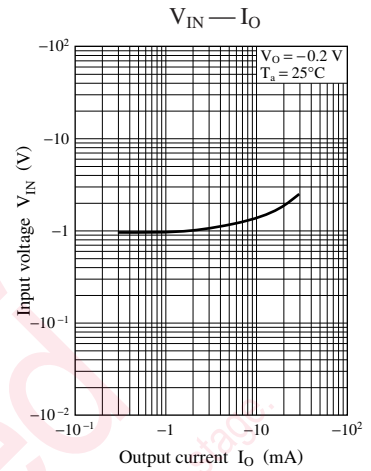
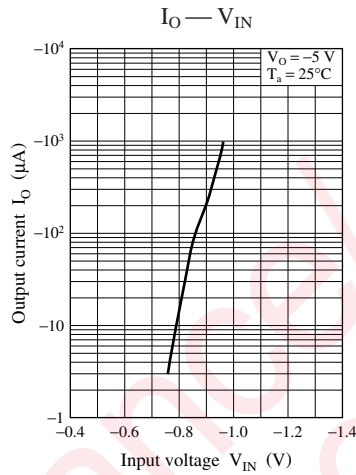
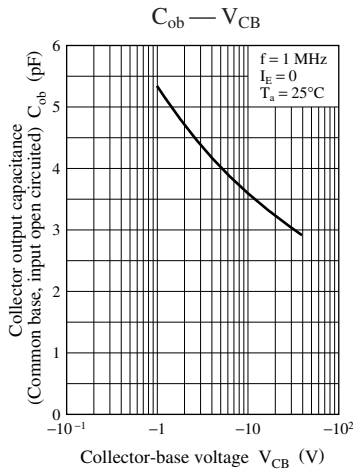


Characteristics charts of UNR911EJ

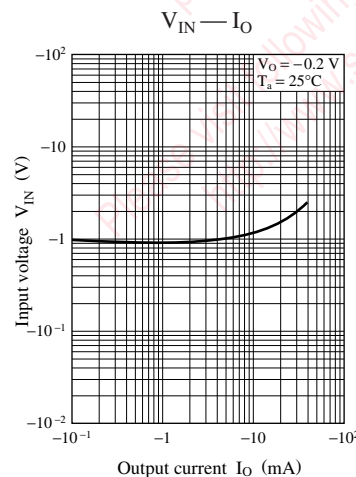
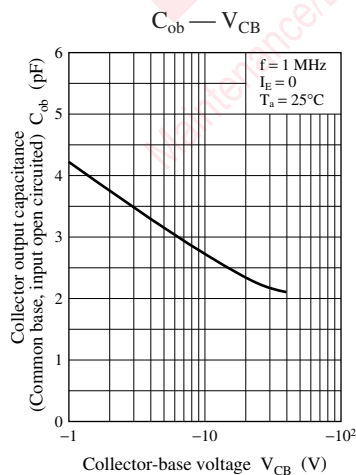
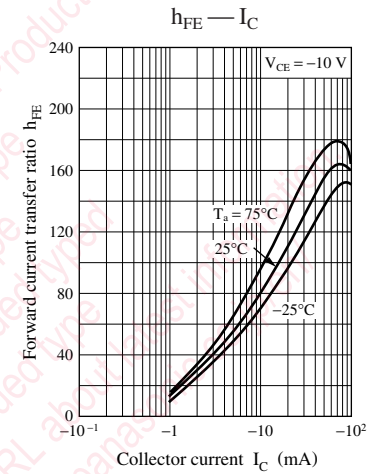
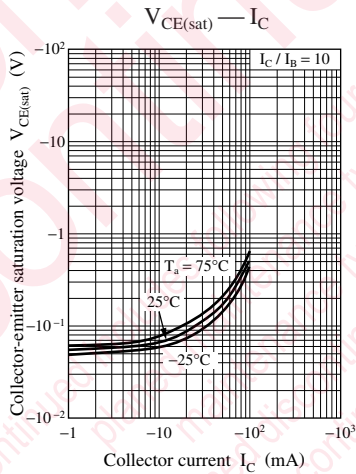
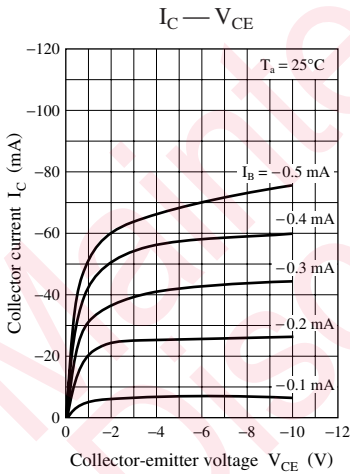


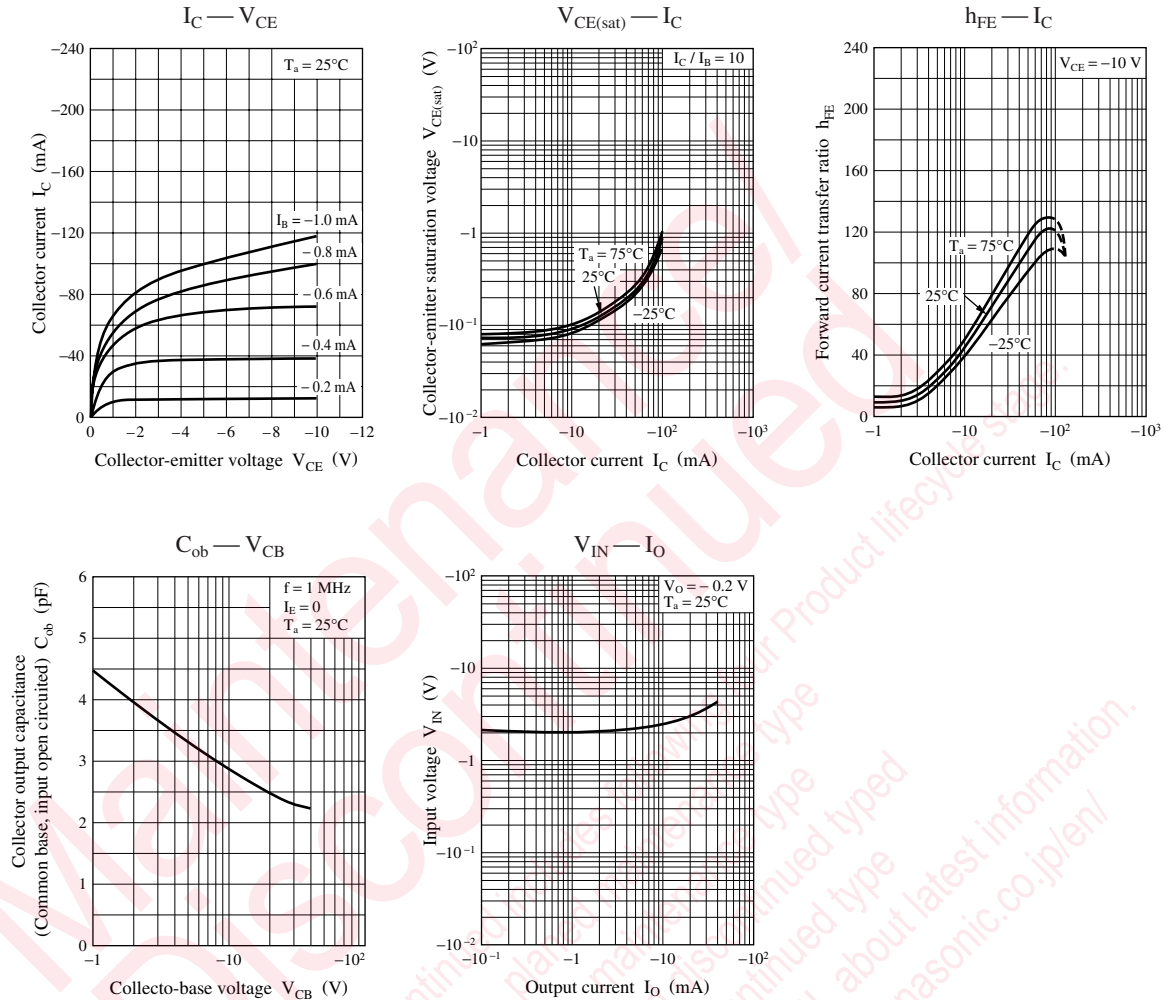
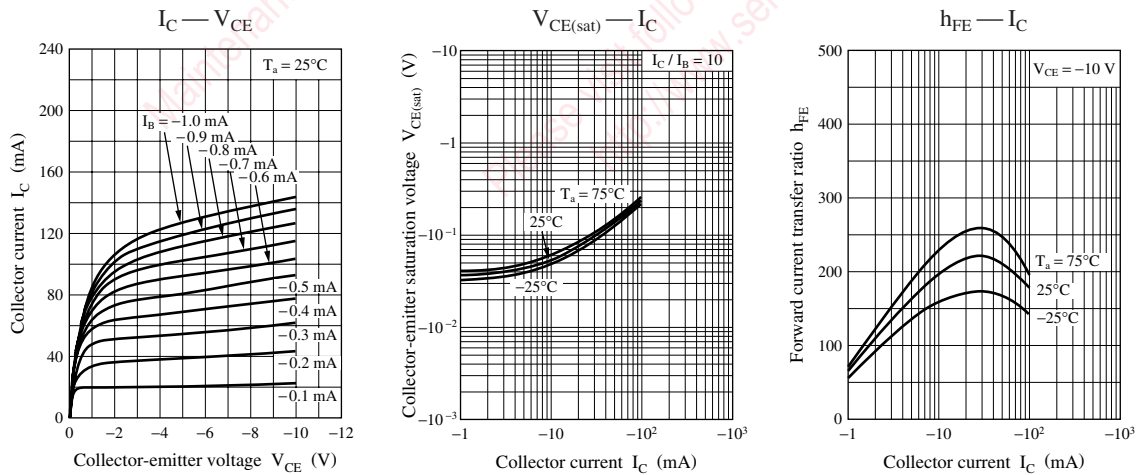
Characteristics charts of UNR911FJ

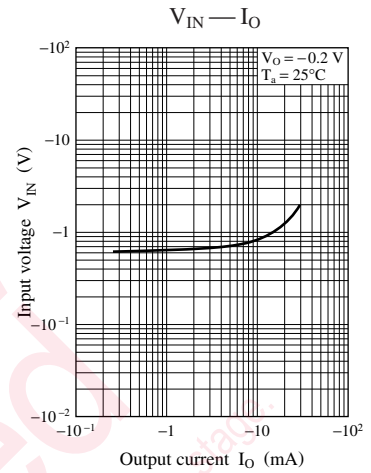
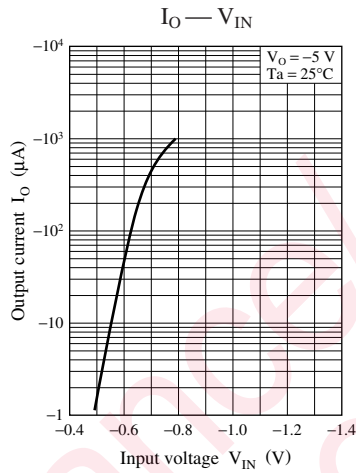
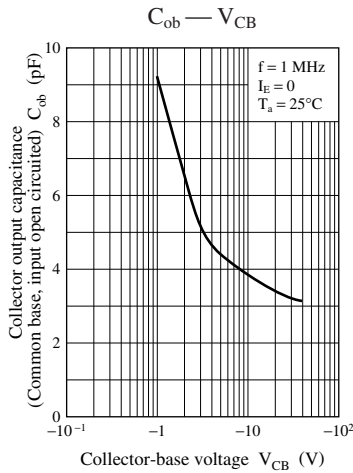




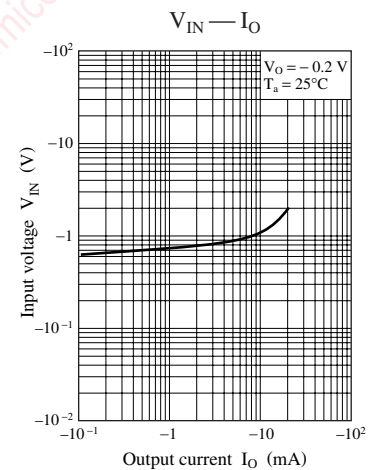
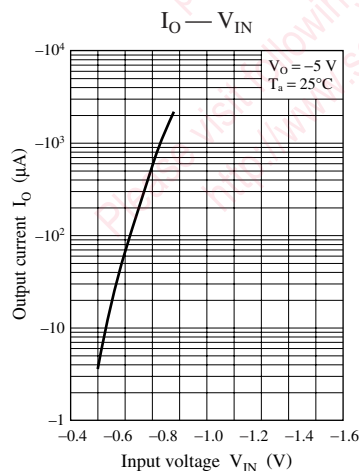
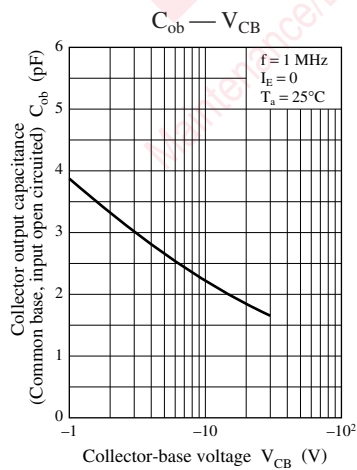
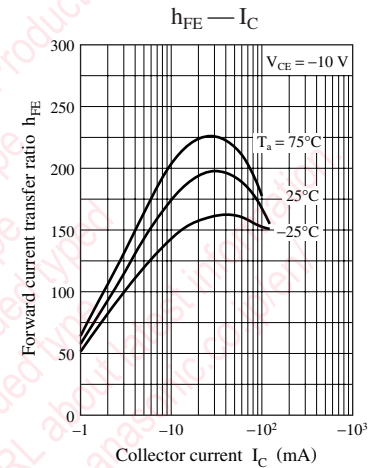
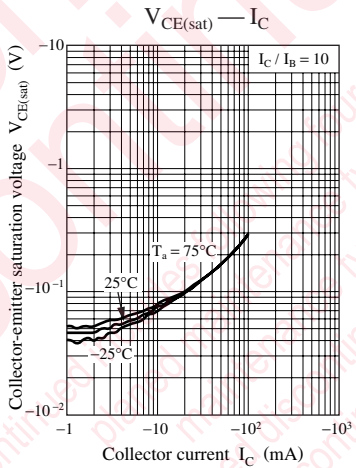
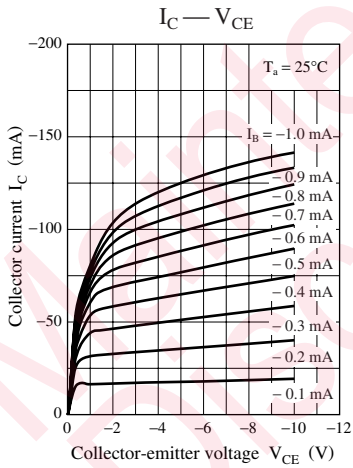
Characteristics charts of UNR911HJ



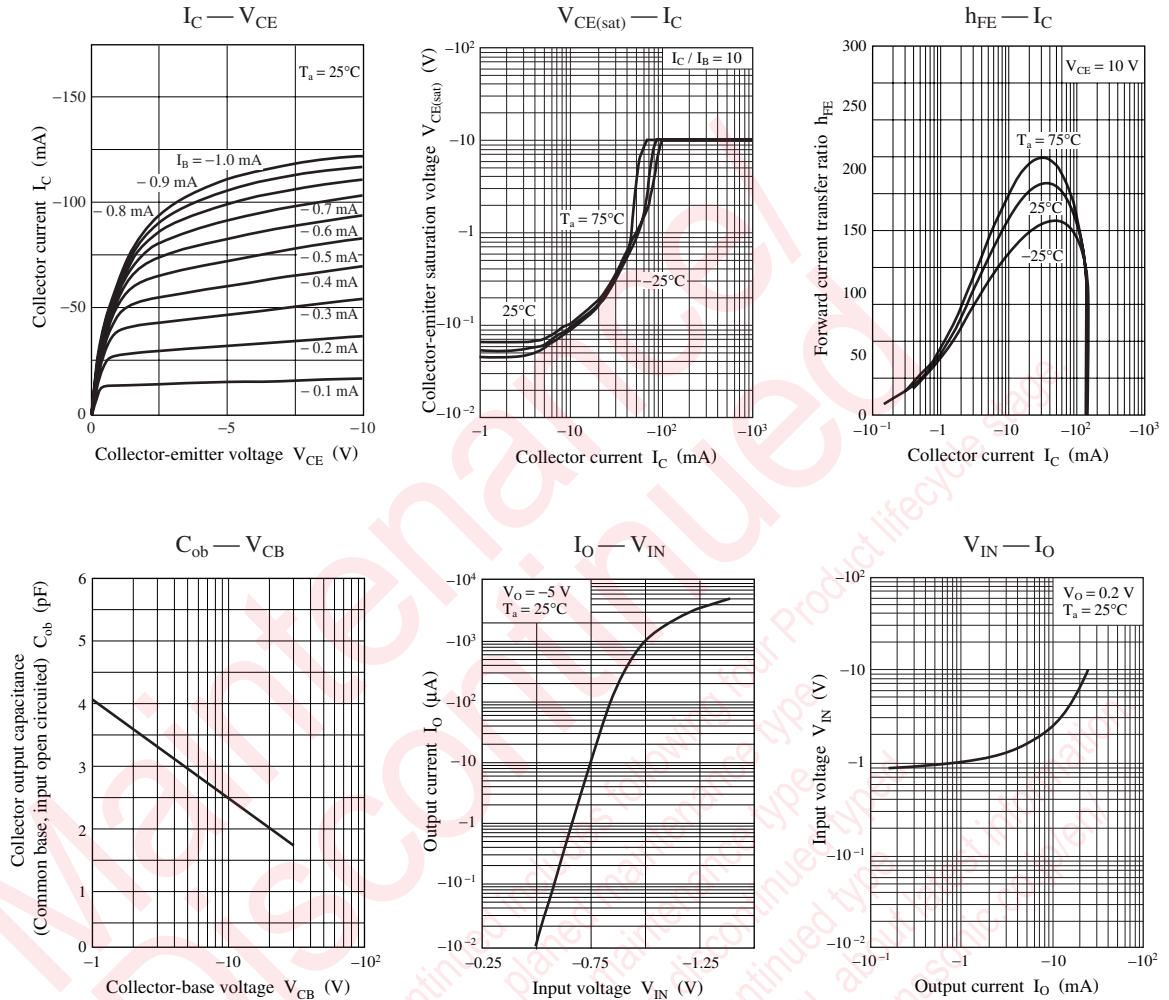
Characteristics charts of UNR911LJ**Characteristics charts of UNR911MJ**



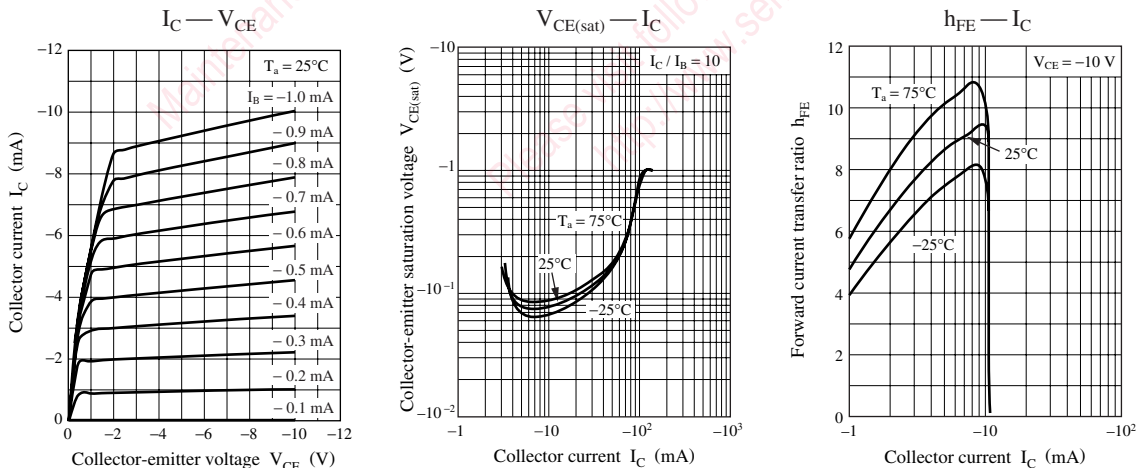
Characteristics charts of UNR911NJ

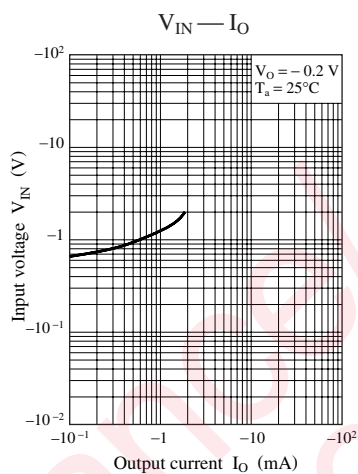
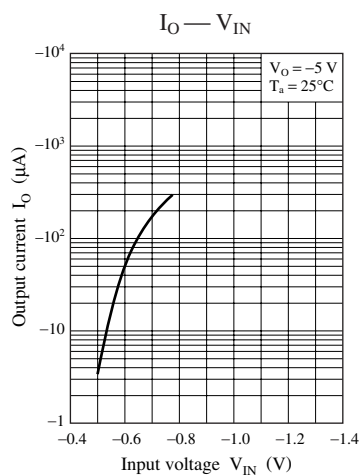


Characteristics charts of UNR911TJ



Characteristics charts of UNR911VJ





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